Electronic supplementary information

## Stabilizing organic photocathodes by lowtemperature atomic layer deposition of TiO<sub>2</sub>

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Figure S1. a) Histogram of coincident time-of-flight and energy events for ALD TiO<sub>2</sub> grown at 80 °C with TDMAT and H<sub>2</sub>O on silicon wafers showing hydrogen, carbon, nitrogen, both isotopes of oxygen, silicon and titanium as well as copper from the primary beam for a 90 nm thick TiO<sub>2</sub> film on Si. b) Concentration depth profiles for the 90 nm thick TiO<sub>2</sub> samples from a). Values in Table 1 were averaged from the pink marked region that is presented in a linear plot in c). No elemental losses were observed during the measurements. Hydrogen, carbon and nitrogen concentrations increase slightly towards the interface.

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Figure S2. Constant potential (0 V vs RHE) measurements of Cul/P3HT:PCBM/TiO<sub>2</sub>/RuO<sub>x</sub> photocathodes with varied ALD TiO<sub>2</sub> thicknesses as labeled, under steady illumination that was periodically blocked to observe the current in dark. All measurements were performed in pH 5 electrolyte under simulated one-sun illumination.



Figure S3. Cyclic voltammetry scans of films of a) P3HT and b) PCBM deposited onto bare FTO substrates (black) and onto Cul-coated FTO (red). Scan rates = 100 mV/s, electrolyte pH = 5. Around 5-10 repeated scan cycles were performed for each, and the data presented here are representative behaviours observed during this period.



**Figure S4.** Photographs of photocathodes after extended testing. Devices with 75 nm  $TiO_2$  tested for (A) 90 min. and (B) 300 min. in pH 5 electrolyte at 0 V vs RHE. Sample degradation initiates at the edge of the epoxy, suggesting that the encapsulation strategy may stress the  $TiO_2$  overlayer and cause defects through which electrolyte can penetrate. The purple P3HT:PCBM film gradually delaminates from the FTO surface, indicative of dissolution of the Cul underlayer.



Figure S5. Potential measurement during RuO<sub>x</sub> catalyst photo-electrodeposition on devices of varied TiO<sub>2</sub> thickness. A reducing galvanostatic current density of -36  $\mu$ A/cm<sup>2</sup> was fixed for 900 s total, and simulated one-sun illumination was applied constantly except when briefly blocked during the moments labeled by asterisks (\*).



**Figure S6**. Schematic illustration of charge transport and transfer processes which are sensitive to  $TiO_2$  overlayer thickness. 1) When  $TiO_2$  is thin or absent,  $H_2O$  can penetrate the blend, and red-ox behaviours attributable to CuI reduction can be seen in the CVs. This corrosion process also inhibits catalyst electrodeposition. 2) With a  $TiO_2$  overlayer, electrons are efficiently collected from the blend and transported to the surface where they drive the catalyst electrodeposition, forming a  $RuO_x$  film. 3) The full device with catalyst drives photoelectrochemical hydrogen evolution. Note that photoexcitation of electrons in P3HT is not depicted here, and the illustration is not to scale.



**Figure S7**. Scanning electron microscopy imaging of cleaved photocathode cross-sections for a Cul/P3HT:PCBM/TiO<sub>2</sub>/RuO<sub>x</sub> device with 75 nm ALD TiO<sub>2</sub>. a) Secondary electron imaging. b) Electron backscatter imaging. The bright areas in the backscatter image arise from the enhanced scattering from heavy atoms such as metals (Ti, Ru, and Sn). There is no clear evidence of TiO<sub>2</sub> penetration into the polymer film.



Figure S8. High-resolution SEM cross-section image of a Cul/P3HT:PCBM/TiO<sub>2</sub> device.